
2SJ172

Silicon P-Channel MOS FET

HITACHI

November 1996

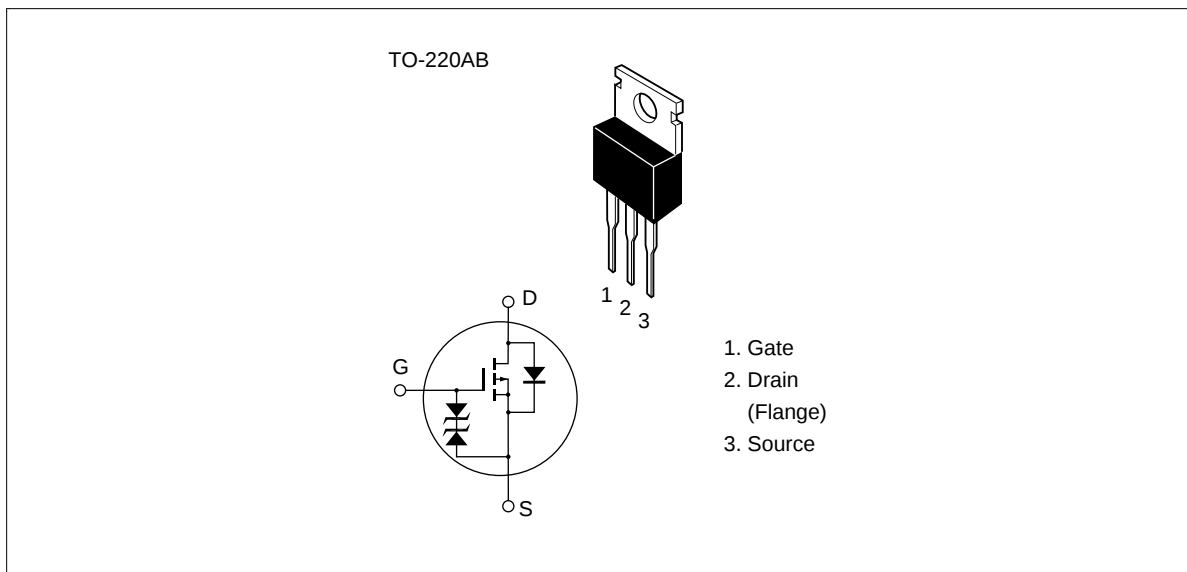
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline



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Absolute Maximum Ratings (Ta = 25°C)

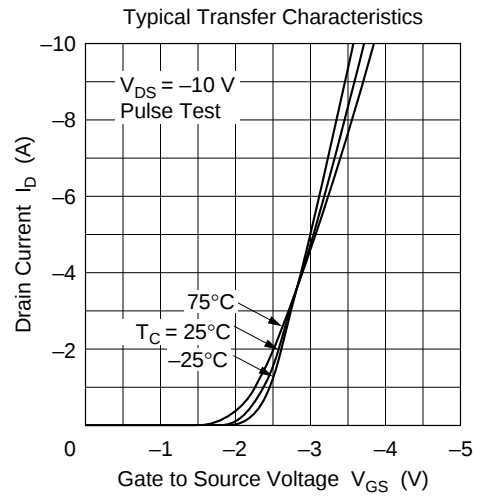
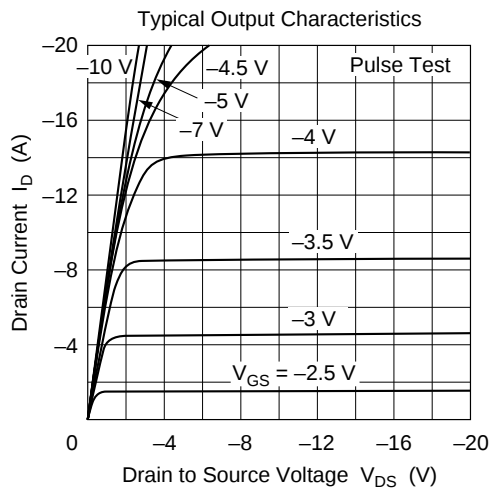
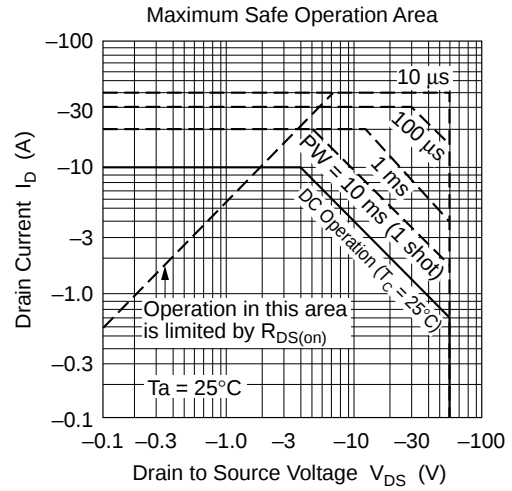
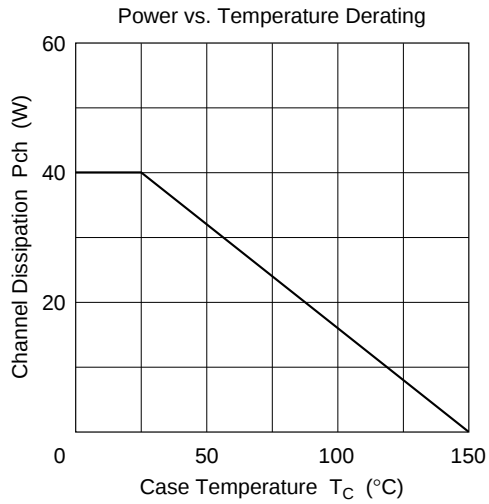
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	-60	V
Gate to source voltage	V_{GS}	±20	V
Drain current	I_D	-10	A
Drain peak current	$I_{D(pulse)}^{*1}$	-40	A
Body to drain diode reverse drain current	I_{DR}	-10	A
Channel dissipation	P_{ch}^{*2}	40	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

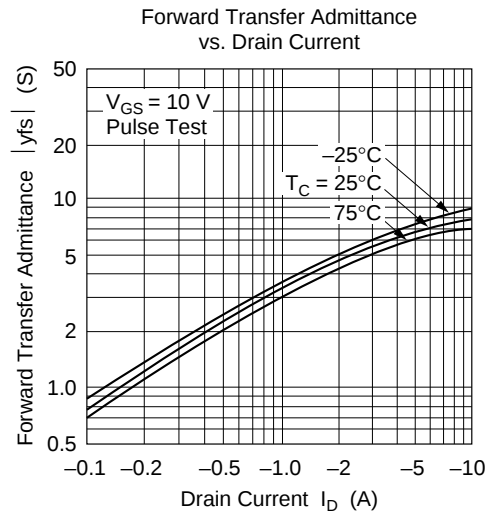
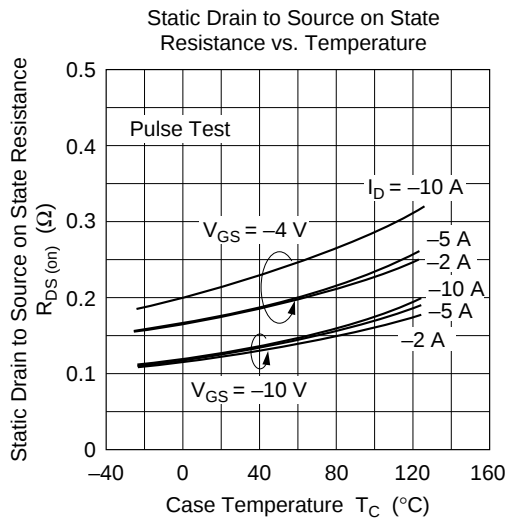
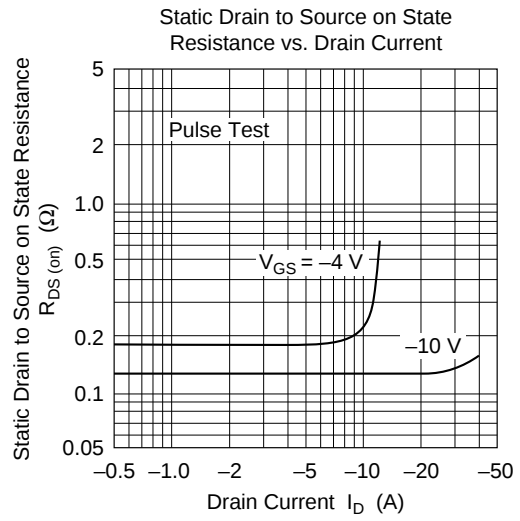
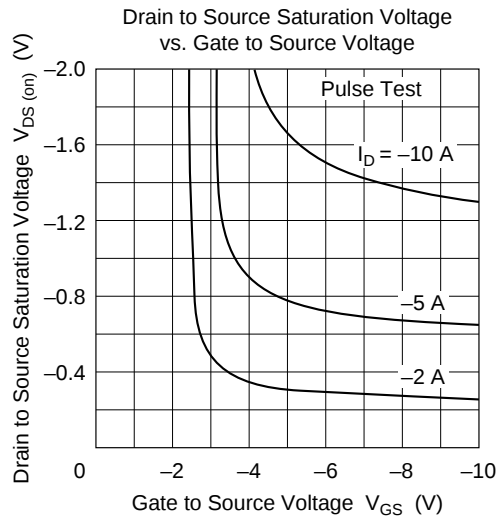
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

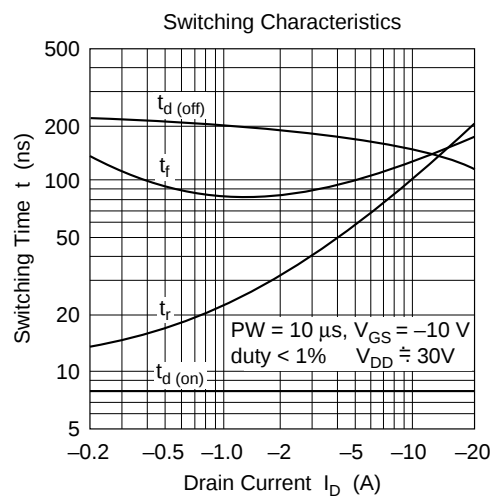
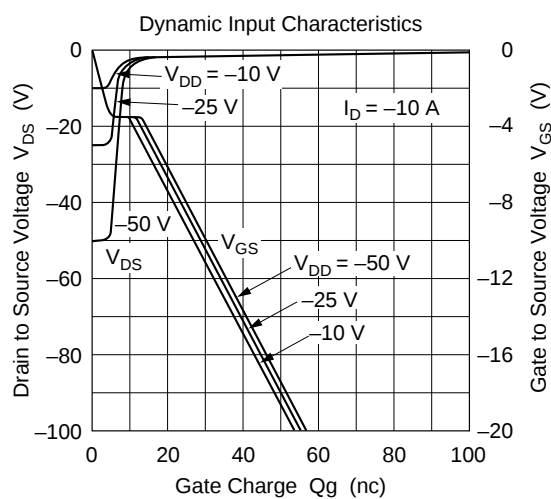
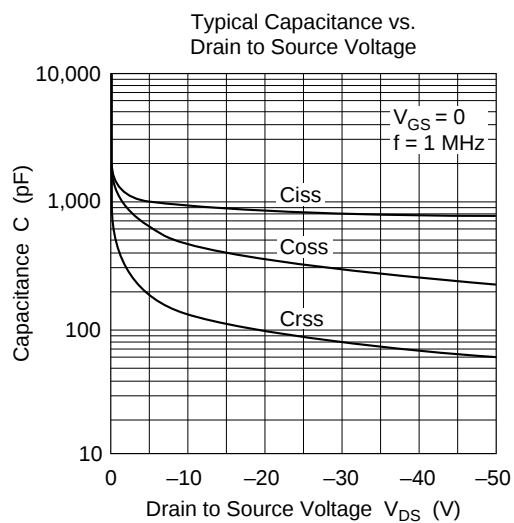
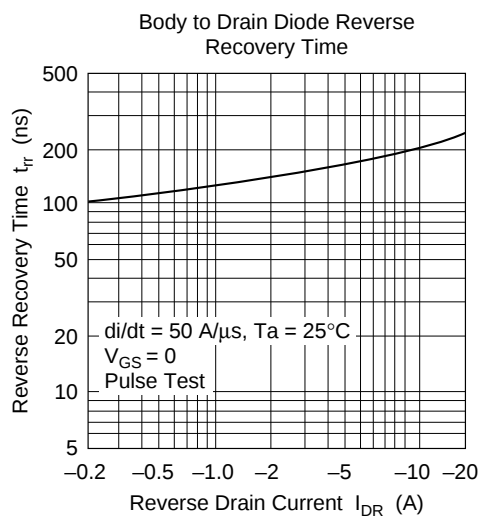
Electrical Characteristics (Ta = 25°C)

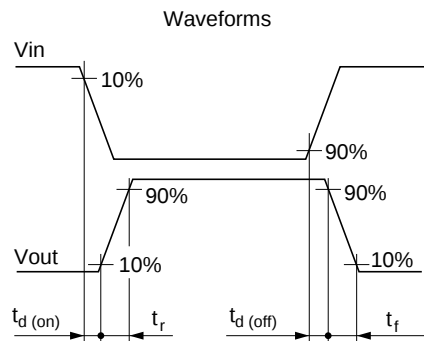
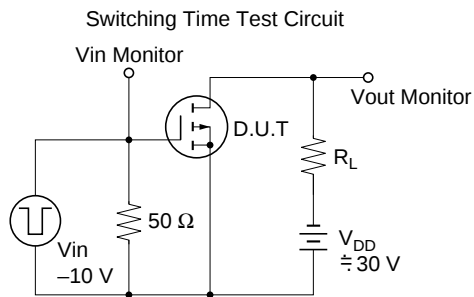
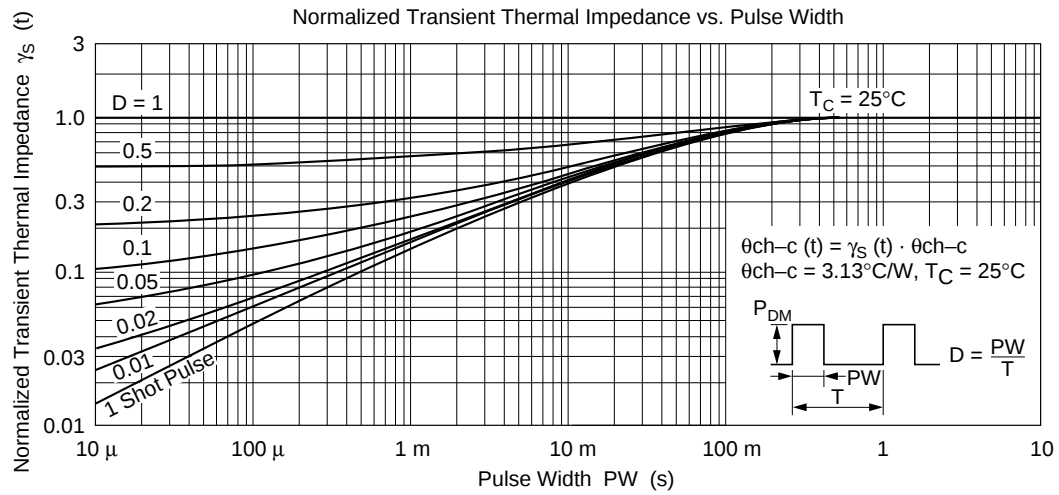
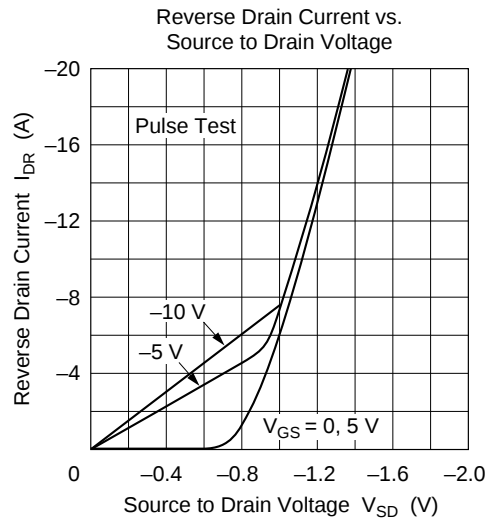
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DS}$	-60	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = -50 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.13	0.18	Ω	$I_D = -5 \text{ A}$, $V_{GS} = -10 \text{ V}^{*1}$
			0.18	0.25		$I_D = -5 \text{ A}$, $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	4.0	6.5	—	S	$I_D = -5 \text{ A}$, $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	900	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	460	—	pF	
Reverse transfer capacitance	C_{rss}	—	130	—	pF	
Turn-on delay time	$t_{d(on)}$	—	8	—	ns	$I_D = -5 \text{ A}$, $V_{GS} = -10 \text{ V}$, $R_L = 6 \Omega$
Rise time	t_r	—	65	—	ns	
Turn-off delay time	$t_{d(off)}$	—	170	—	ns	
Fall time	t_f	—	105	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.1	—	V	$I_F = -10 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	200	—	ns	$I_F = -10 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu s$

Note 1. Pulse test









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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071